



IRF530FP

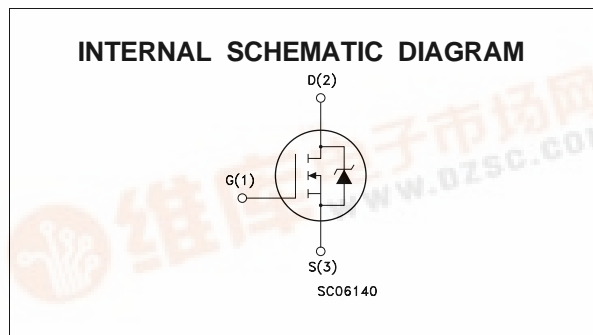
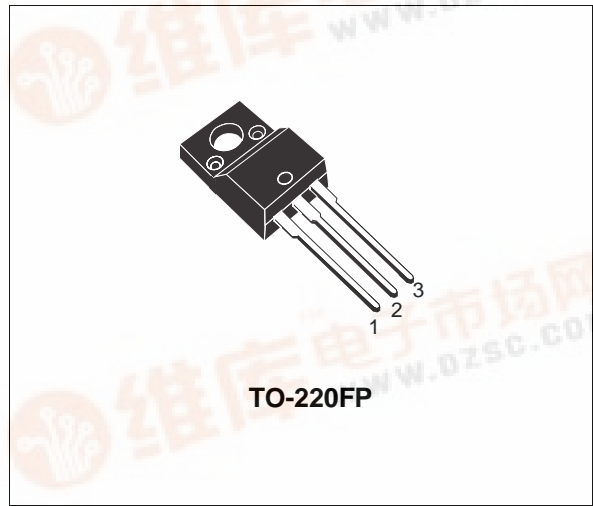
N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTOR

TYPE	V _{DSS}	R _{DS(on)}	I _D
IRF530FP	100 V	< 0.16 Ω	10 A

- TYPICAL R_{DS(on)} = 0.12 Ω
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW GATE CHARGE
- AVALANCHE RUGGED TECHNOLOGY
- APPLICATION ORIENTED CHARACTERIZATION
- HIGH CURRENT CAPABILITY
- 175°C OPERATING TEMPERATURE

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- DC-DC & DC-AC CONVERTER
- AUTOMOTIVE ENVIRONMENT (INJECTION, ABS, AIR-BAG, LAMP DRIVERS, Etc)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	100	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	100	V
V _{GS}	Gate-source Voltage	± 20	V
I _D	Drain Current (continuous) at T _c = 25 °C	10	A
I _D	Drain Current (continuous) at T _c = 100 °C	7	A
I _{DM} (•)	Drain Current (pulsed)	64	A
P _{tot}	Total Dissipation at T _c = 25 °C	35	W
	Derating Factor	0.23	W/°C
V _{ISO}	Insulation Withstand Voltage (DC)	2000	V
T _{stg}	Storage Temperature	-65 to 175	°C
T _j	Max. Operating Junction Temperature	175	°C

(•) Pulse width limited by safe operating area

IRF530FP

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	4.28	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5	°C/W
R _{thc-sink}	Thermal Resistance Case-sink	Typ	0.5	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose		300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max, δ < 1%)	16	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 25 V)	85	mJ

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA V _{GS} = 0	600			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _c = 125 °C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	2	3	4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V I _D = 8 A		0.12	0.16	Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} × R _{DS(on)max} V _{GS} = 10 V	10			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} I _D = 8 A	5	8		S
C _{iss}	Input Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		950	1300	pF
C _{oss}	Output Capacitance			150	270	pF
C _{rss}	Reverse Transfer Capacitance			50	70	pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 50\text{ V}$ $I_D = 8\text{ A}$		12	16	ns
t_r	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		20	28	ns
Q_g	Total Gate Charge	$V_{DD} = 80\text{ V}$ $I_D = 16\text{ A}$ $V_{GS} = 10\text{ V}$		32	44	nC
Q_{gs}	Gate-Source Charge			9		nC
Q_{gd}	Gate-Drain Charge			13		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 80\text{ V}$ $I_D = 16\text{ A}$		11	15	ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		12	17	ns
t_c	Cross-over Time			25	35	ns

SOURCE DRAIN DIODE

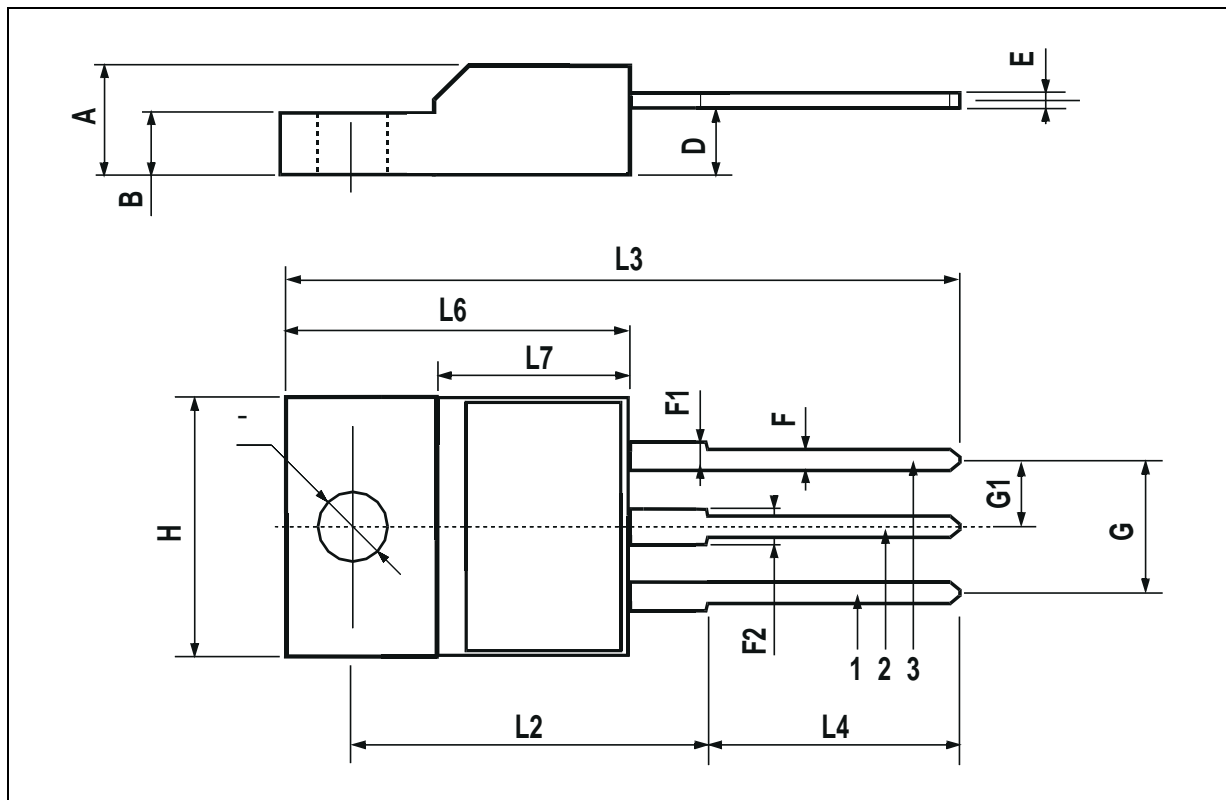
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				16	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				64	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 16\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 16\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		150		ns
Q_{rr}	Reverse Recovery Charge			0.8		μC
I_{RRM}	Reverse Recovery Current			10		A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

TO-220FP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
∅	3		3.2	0.118		0.126



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